

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07424 D T-33-07

SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC522

2SC524

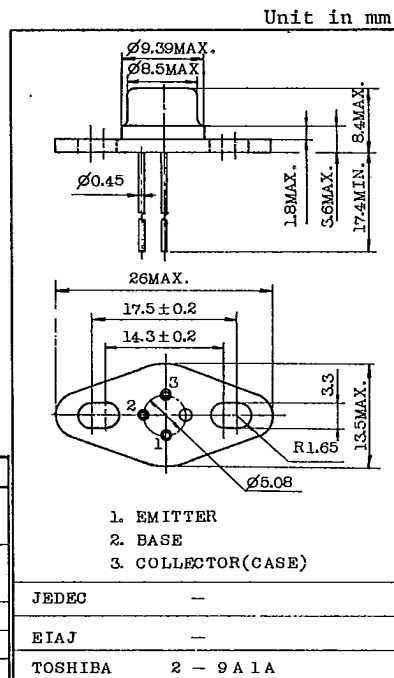
HIGH FREQUENCY AMPLIFIER APPLICATIONS.
HIGH VOLTAGE SWITCHING APPLICATIONS.
REGULATOR APPLICATIONS.

FEATURES:

- High Breakdown Voltage : $V_{CE0}=100V$ (2SC522)
: $V_{CE0}=60V$ (2SC524)
- Useful attachment for Heat sink.
- Various Uses for Medium Power
: $I_C=1.5A$ (Max.), $P_C=10W$ (Max.)

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	140	V
2SC524		100	
Collector-Emitter Voltage	V_{CEO}	100	V
2SC524		60	
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Base Current	I_B	300	mA
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	10	W
Junction Temperature	T_j	175	$^\circ C$
Storage Temperature Range	T_{stg}	-65~175	$^\circ C$



Mounting kit No. AC26C
Weight : 3.7g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

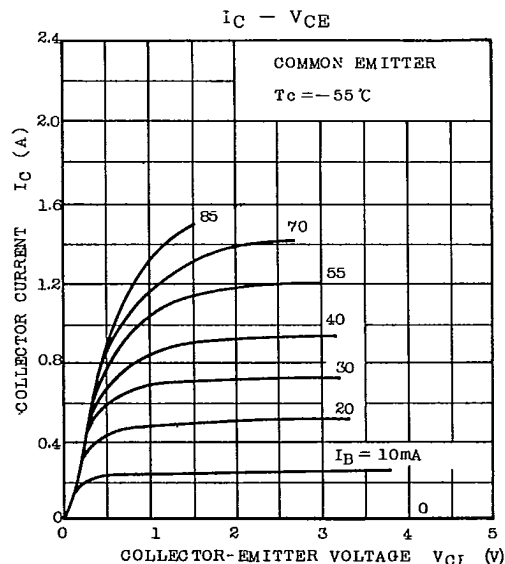
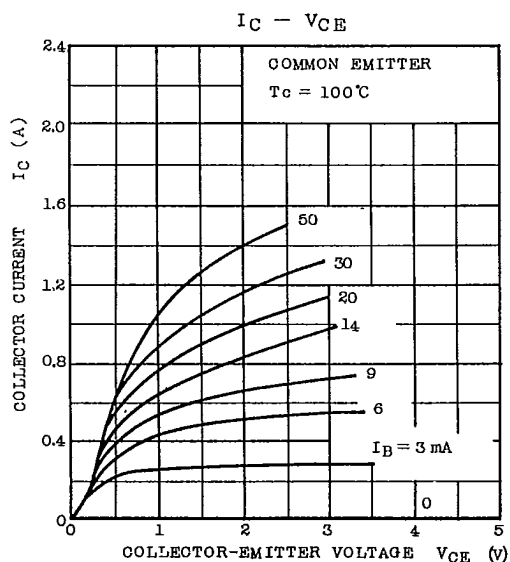
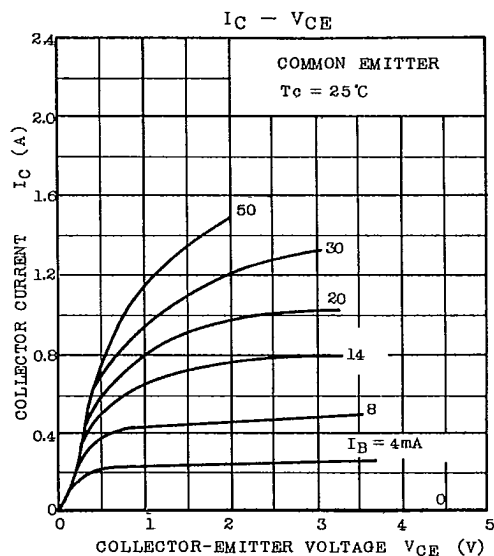
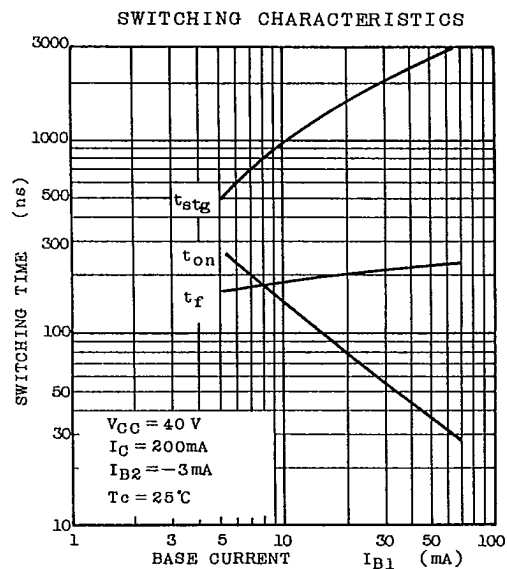
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=30V, I_E=0$	-	-	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	10	μA
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE}=2V, I_C=200mA$	30	-	150	
	$h_{FE}(2)$	$V_{CE}=5V, I_C=1A$	15	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=20mA$	-	0.2	0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=200mA, I_B=20mA$	-	0.8	1.0	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=30mA$	20	60	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	25	40	pF
Switching Time	Turn-on Time		-	0.13	-	μs
	Storage Time		-	3	-	
	Fall Time		-	0.2	-	

Note : $h_{FE}(1)$ Classification R : 30~90, 0 : 50~150

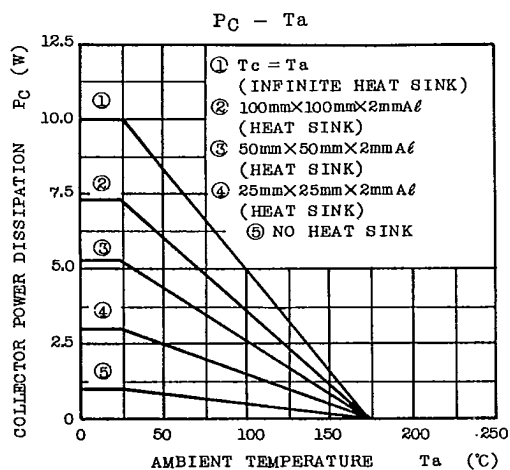
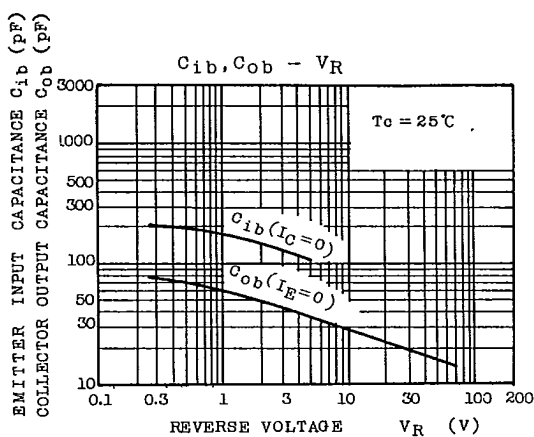
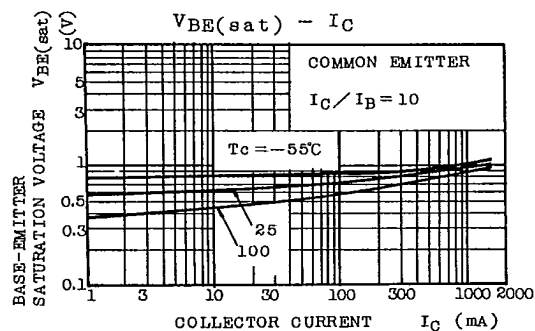
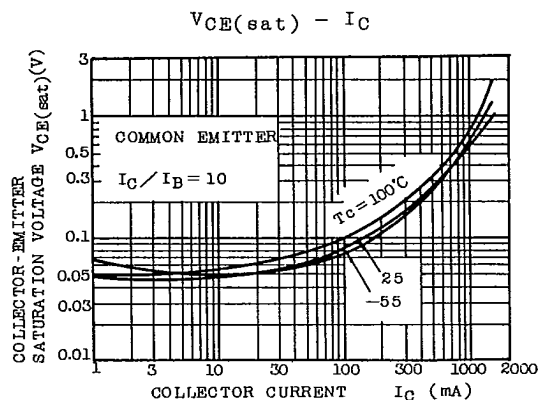
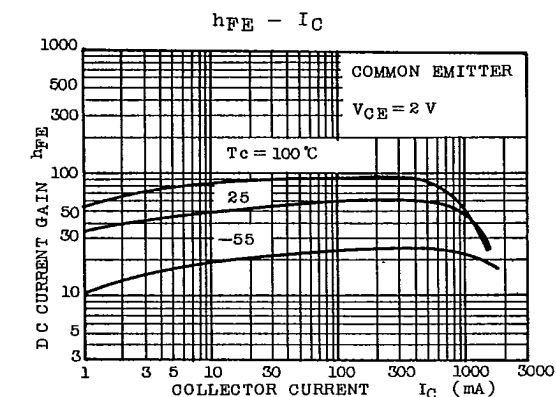
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